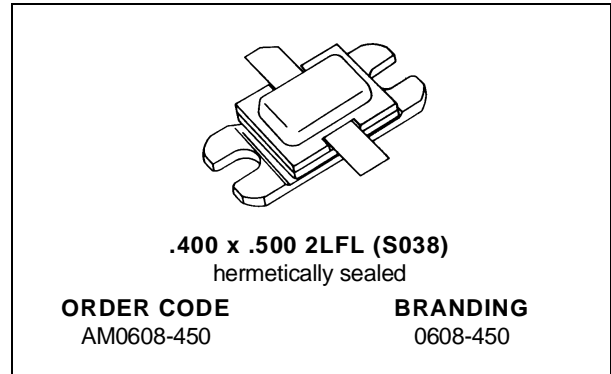


RF & MICROWAVE TRANSISTORS AVIONICS APPLICATIONS

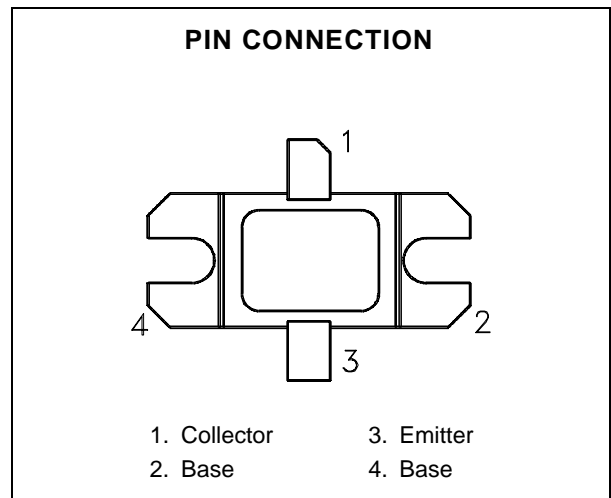
PRELIMINARY DATA

- REFRACTORY/GOLD METALLIZATION
- INPUT MATCHING
- OVERLAY GEOMETRY
- METAL/CERAMIC HERMETIC PACKAGE
- P_{OUT} = 445 W MIN. WITH 6.9 dB GAIN



DESCRIPTION

The AM0608-450 is an internally-matched, common base silicon bipolar device optimized pulsed application in the 600 - 750 MHz frequency range. Housed in the industry-standard BIGPAC™ metal/ceramic package, this device uses a refractory/gold overlay die geometry for ruggedness and long-term reliability.



ABSOLUTE MAXIMUM RATINGS (T_{case} = 25°C)

Symbol	Parameter	Value	Unit
P _{DISS}	Power Dissipation* (T _C ≤ 50°C)	1500	W
I _C	Device Current*	32	A
V _{CC}	Collector-Supply Voltage*	55	V
T _J	Junction Temperature (Pulsed RF Operation)	250	°C
T _{STG}	Storage Temperature	- 65 to +200	°C

THERMAL DATA

R _{TH(j-c)}	Junction-Case Thermal Resistance*	0.13	°C/W
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*Applies only to rated RF amplifier operation

AM0608-450

ELECTRICAL SPECIFICATIONS (T_{case} = 25°C)

STATIC

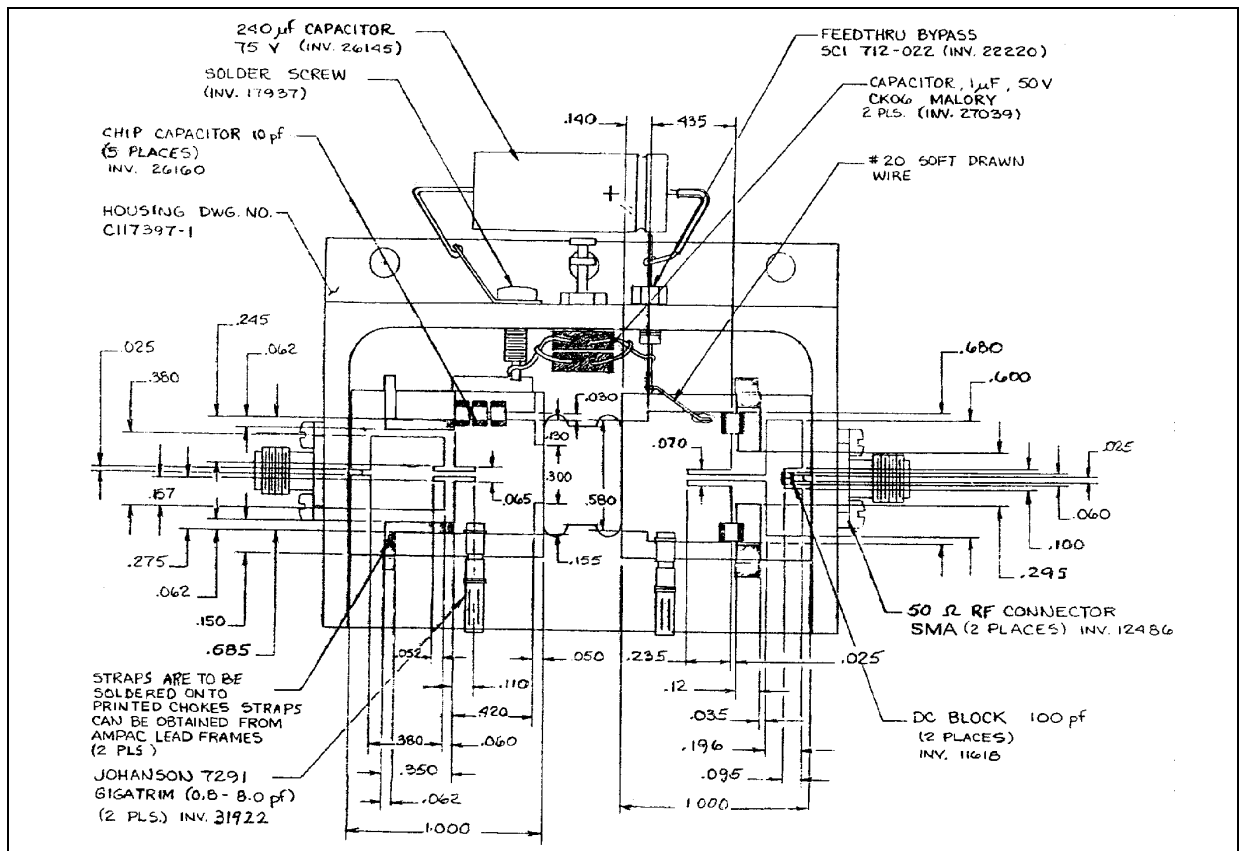
Symbol	Test Conditions		Value			Unit
			Min.	Typ.	Max.	
BV _{CBO}	I _C = 50mA	I _E = 0mA	65	—	—	V
BV _{EBO}	I _E = 5mA	I _C = 0mA	3.5	—	—	V
BV _{CER}	I _C = 50mA	R _{BE} = 10Ω	65	—	—	V
I _{CES}	V _{CE} = 50V		—	—	35	mA
I _{CBO}	V _{CB} = 50V		—	—	25	mA
h _{FE}	V _{CE} = 5V	I _C = 1A	15	—	300	—

DYNAMIC

Symbol	Test Conditions			Value			Unit
				Min.	Typ.	Max.	
P _{OUT}	f = 600 — 750MHz	P _{IN} = 90W	V _{CC} = 50V	445	—	—	W
η _c	f = 600 — 750MHz	P _{IN} = 90W	V _{CC} = 50V	35	—	—	%
G _p	f = 600 — 750MHz	P _{IN} = 90W	V _{CC} = 50V	6.9	—	—	dB

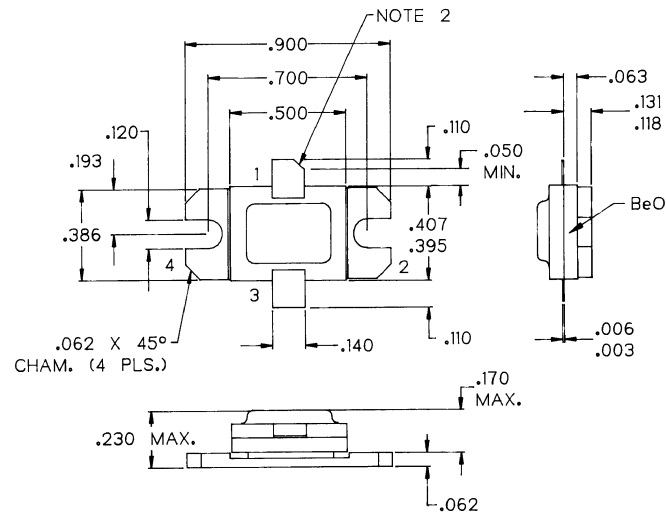
Note: Pulse Width = 10μS
Duty Cycle = 1%

TEST CIRCUIT



PACKAGE MECHANICAL DATA

Ref.: Dwg. No.: J135066F



NOTES:

1. ALL TOLERANCE $\pm .010$ EXCEPT WHERE NOTED;
DIMENSIONS IN INCHES.
2. COLLECTOR LEAD CHAMFER 45° NOM. X .040 NOM.

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